TPS22996 5.5V, 4A, 14mΩ On-Resistance Dual-Channel Load Switch

1 Features

- Integrated dual-channel load switch
- V_{IN} voltage range: 0.6V to V_{BIAS}
- V_{BIAS} voltage range: 2.5V to 5.5V
- On-resistance: 14mΩ (typical)
- 4A maximum continuous switch current per channel
- Quiescent current:
  - I_Q = 16µA (typical, both channels) at V_{IN} = V_{BIAS} = 5V
  - I_Q = 13µA (typical, single channel) at V_{IN} = V_{BIAS} = 5V
- Control input threshold enables use of 1.2V, 1.8V, 2.5V, and 3.3V logic
- Configurable rise time
- Thermal shutdown
- Quick Output Discharge (QOD) (optional)

2 Applications

- PC and notebooks
- Set-top boxes and residential gateways
- Telecom systems
- Solid-state drives (SSD)

3 Description

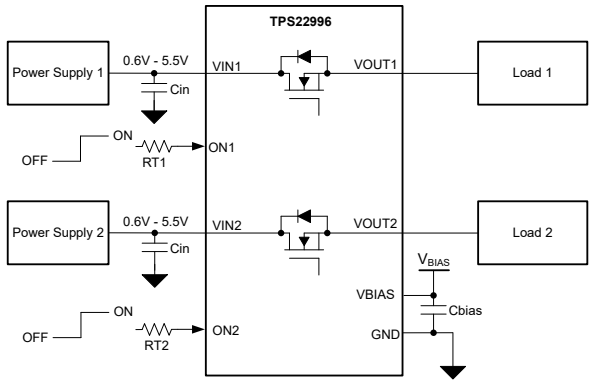
The TPS22996 product family consists of two devices: TPS22996 and TPS22996N. Each device is a dual-channel load switch with controlled turnon. The device contains two N-channel MOSFETs that can operate over an input voltage range of 0.6V to 5.5V, and can support a maximum continuous current of 4A per channel. Each switch is independently controlled by an on and off input (ON1 and ON2), which can interface directly with low-voltage control signals. The TPS22996 is capable of thermal shutdown when the junction temperature is above the threshold, turning the switch off. The switch turns on again when the junction temperature stabilizes to a safe range. The TPS22996 also offers an optional integrated 230Ω on-chip load resistor for quick output discharge when the switch is turned off.

The TPS22996 is available in a small, space-saving 2.1mm × 1.6mm 8-DRL package with leads to enable low cost manufacturing. The device is characterized for operation over the free-air temperature range of –40°C to 105°C.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)
TPS22996	DRL (SOT, 8)	2.10mm × 1.60mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.



Application Circuit

Table of Contents

4 Device Comparison Table

DEVICE	R_{ON} AT V_{IN} = V_{BIAS} = 5V (TYPICAL)	QUICK OUTPUT DISCHARGE	MAXIMUM OUTPUT CURRENT
TPS22996	14mΩ	Yes	4A
TPS22996N	14mΩ	No	4A

5 Pin Configuration and Functions

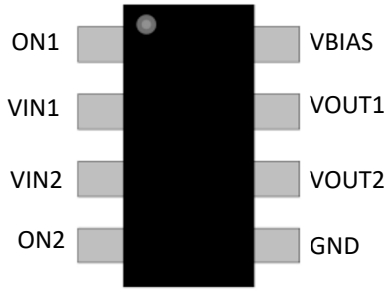


Figure 5-1. DRL Package, 8-Pin SOT (Top View)

Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	ON1	I	Active-high switch 1 control input. Connect series resistor to set slew rate. Do not leave floating.
2	VIN1	I	Switch 1 input. Recommended voltage range for these pins for optimal R_{ON} performance is 0.6V to V_{BIAS}. Place an optional decoupling capacitor between these pins and GND to reduce V_{IN1} dip during turnon of the channel.
3	VIN2	I	Switch 2 input. Recommended voltage range for these pins for optimal R_{ON} performance is 0.6V to V_{BIAS}. Place an optional decoupling capacitor between these pins and GND to reduce V_{IN1} dip during turnon of the channel.
4	ON2	I	Active-high switch 2 control input. Connect series resistor to set Slew Rate. Do not leave floating.
5	GND	I	Device ground.
6	VOUT2	I	Switch 2 output.
7	VOUT1	I	Switch 1 output.
8	VBIAS	I	Bias voltage. Power supply to the device. Recommended voltage range for this pin is 2.5V to 5.5V.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
$V_{IN1,2}$	Input voltage	–0.3	6	V
$V_{OUT1,2}$	Output voltage	–0.3	6	V
$V_{ON1,2}$	ON pin voltage	–0.3	6	V
V_{BIAS}	Bias voltage	–0.3	6	V
I_{MAX}	Maximum continuous current per channel		4	A
$I_{MAX,PLS}$	Maximum pulsed current switch per channel, pulse <300µs, 3% duty cycle		5.5	A
T_J	Junction temperature		125	°C
T_{stg}	Storage temperature	–65	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins(1)	±2000	V
		Charged device model (CDM), per JEDEC specification JS-002, all pins(2)	±1000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
$V_{IN1,2}$	Input voltage	0.6		V_{BIAS}	V
V_{BIAS}	Bias voltage	2.5		5.5	V
$V_{ON1,2}$	ON pin voltage	0		5.5	V
$V_{OUT1,2}$	Output voltage	0		V_{IN}	V
V_{IH}	High-Level input voltage, ON	1.2		5.5	V
V_{IL}	Low-Level input voltage, ON	0		0.6	V
T_A	Ambient temperature	–40		105	°C

6.4 Thermal Information

THERMAL METRIC(1)		TPS22996 DRL (SOT) 8 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.8	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	48.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	20.7	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	1	°C/W

6.4 Thermal Information (continued)

THERMAL METRIC[1]		TPS22996 DRL (SOT) 8 PINS	UNIT
Ψ_{JB}	Junction-to-board characterization parameter	20.4	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A	MIN	TYP	MAX	UNIT
Power Supplies and Currents								
$I_{Q,VBIAS}$	V_{BIAS} quiescent current (both channels)	$I_{OUT1} = I_{OUT2} = 0$ mA, $V_{IN1,2} = V_{ON1,2} = 5$ V		-40°C to 85°C		16	22	µA
				-40°C to 105°C			23	µA
	V_{BIAS} quiescent current (single-channel)	$I_{OUT1} = I_{OUT2} = 0$ mA, $V_{ON2} = 0$ V, $V_{IN1,2} = V_{IN1} = 5$ V		-40°C to 85°C		13	20	µA
				-40°C to 105°C			22	µA
$I_{SD,VBIAS}$	V_{BIAS} shutdown current	$V_{ON1,2} = 0$ V, $V_{OUT1,2} = 0$ V		-40°C to 105°C		0.1	0.5	µA
$I_{SD,VIN}$	V_{IN} shutdown current (per channel)	$V_{ON} = 0$ V, $V_{OUT} = 0$ V	$V_{IN} = 5$ V	-40°C to 85°C		0.010	0.5	µA
				-40°C to 105°C			0.8	µA
			$V_{IN} = 3.3$ V	-40°C to 85°C		0.010	0.5	µA
				-40°C to 105°C			0.8	µA
			$V_{IN} = 1.8$ V	-40°C to 85°C		0.010	0.5	µA
				-40°C to 105°C			0.8	µA
			$V_{IN} = 0.6$ V	-40°C to 85°C		0.001	0.3	µA
				-40°C to 105°C			0.8	µA
I_{ON}	ON pin leakage current		$V_{ON} = 5.5$ V	-40°C to 105°C			0.1	µA
Resistance Characteristics								
R_{ON}	On-Resistance	$I_{OUT} = -200$ mA	$V_{IN} = 5$ V	25°C		14	18	mΩ
				-40°C to 85°C			21	mΩ
				-40°C to 105°C			23	mΩ
			$V_{IN} = 3.3$ V	25°C		14	18	mΩ
				-40°C to 85°C			21	mΩ
				-40°C to 105°C			23	mΩ
			$V_{IN} = 1.8$ V	25°C		14	18	mΩ
				-40°C to 85°C			21	mΩ
				-40°C to 105°C			23	mΩ
			$V_{IN} = 0.6$ V	25°C		14	18	mΩ
				-40°C to 85°C			21	mΩ
				-40°C to 105°C			23	mΩ
R_i	Internal on pin resistance	$V_{ON} = 5$ V	$V_{ON} = 5$V	-40°C to 105°C		11.5		kΩ
R_{PD}	Output pulldown resistance	$V_{IN} = V_{OUT} = 5$ V, $V_{ON} = 0$ V		-40°C to 105°C		230	280	Ω
T_{SD}	Thermal shutdown	Junction temperature rising		-	150	175		°C
$T_{SD,HYS}$	Thermal shutdown hysteresis	Junction temperature falling		-		20		°C

6.6 Switching Characteristics (TPS22996, TPS22996N)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = VON = VBIAS = 5V						
t_{ON}	Turn ON time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		1000		µs
t_{OFF}	Turn OFF time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		2.3		µs
t_R	Rise time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		688		µs
t_F	Fall time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		2.12		µs
t_D	Delay time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		317		µs
VIN = 0.6V, VON = VBIAS = 5V						
t_{ON}	Turn ON time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		588		µs
t_{OFF}	Turn OFF time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		2.3		µs
t_R	Rise time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		215		µs
t_F	Fall time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		2.12		µs
t_D	Delay time	R_L = 10 Ω, C_L = 0.1 µF, I_{ON} = 100 µA		374		µs

6.7 Typical Characteristics: DC

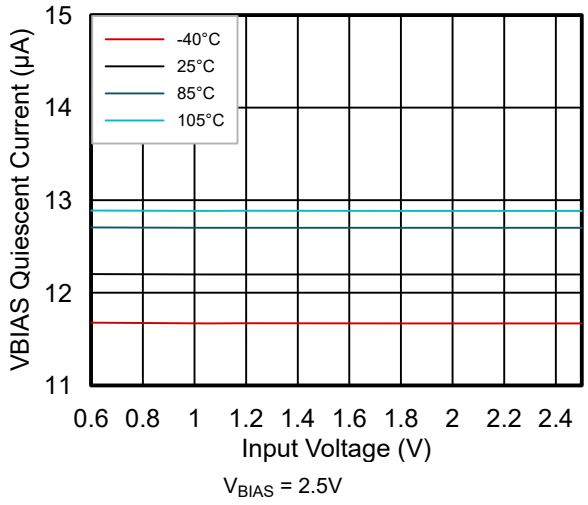


Figure 6-1. V_{BIAS} Quiescent Current vs Input Voltage Single Channel

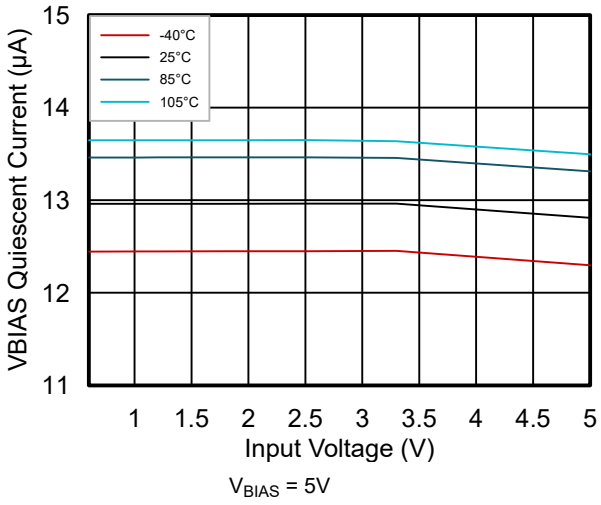


Figure 6-2. V_{BIAS} Quiescent Current vs Input Voltage Single Channel

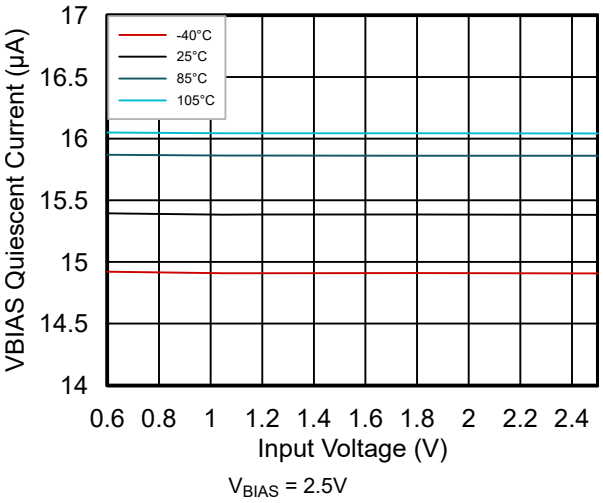


Figure 6-3. V_{BIAS} Quiescent Current vs Input Voltage Both Channels

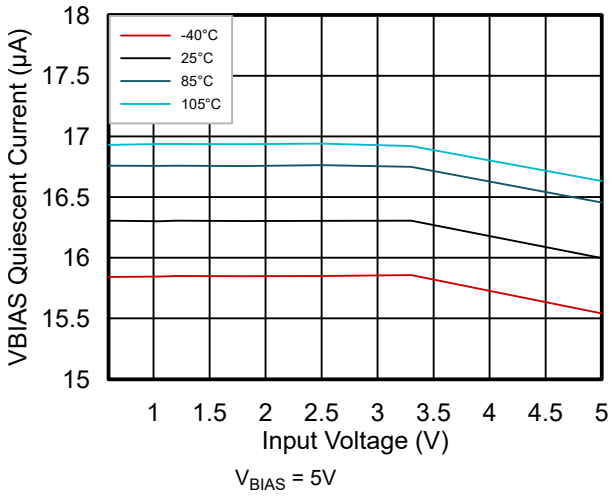


Figure 6-4. V_{BIAS} Quiescent Current vs Input Voltage Both Channels

6.8 Typical Characteristics: AC

C_{IN} = 1µF, C_L = 0.1µF, R_L = 10Ω, V_{ON} = 5V, I_{ON} = 100µA unless otherwise noticed

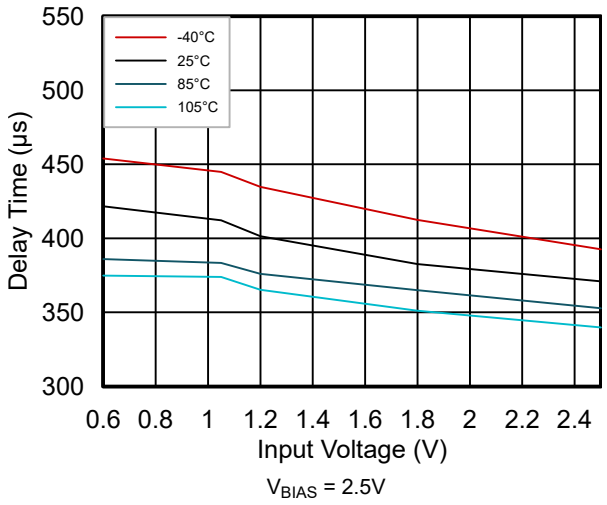


Figure 6-5. Delay Time vs Input Voltage

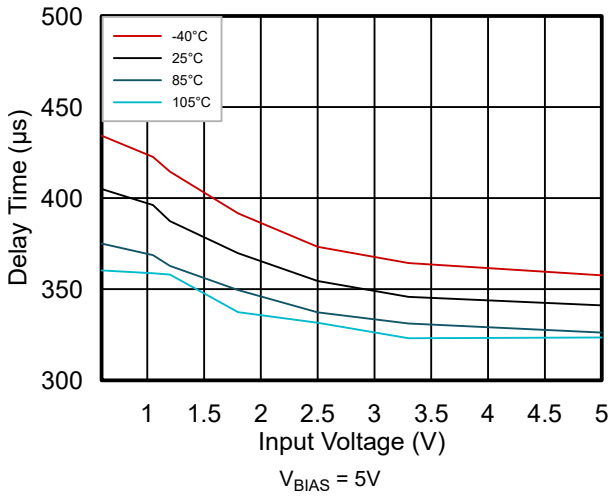


Figure 6-6. Delay Time vs Input Voltage

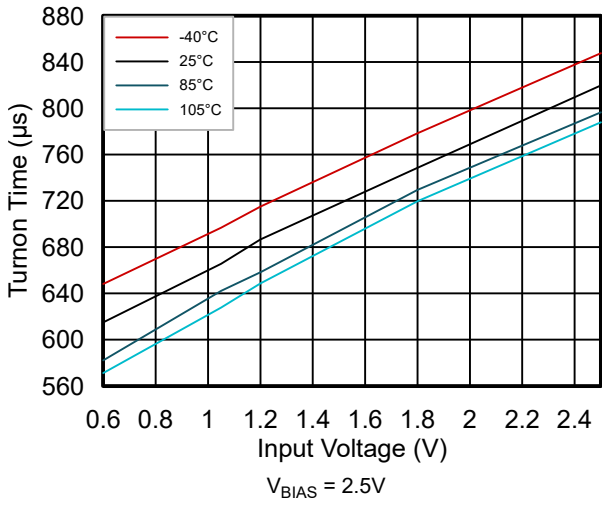


Figure 6-7. Turnon Time vs Input Voltage

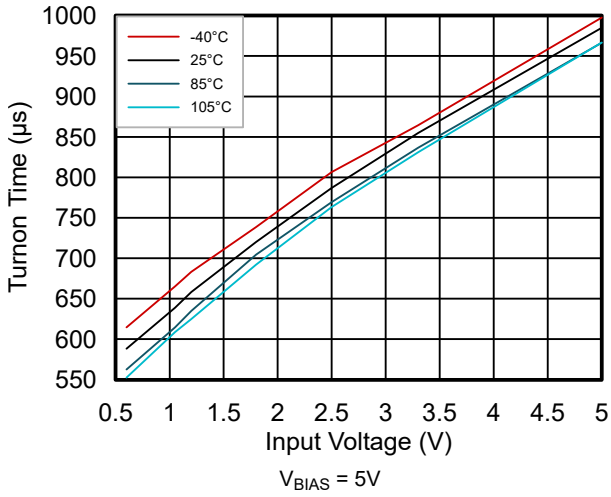


Figure 6-8. Turnon Time vs Input Voltage

6.8 Typical Characteristics: AC (continued)

C_{IN} = 1µF, C_L = 0.1µF, R_L = 10Ω, V_{ON} = 5V, I_{ON} = 100µA unless otherwise noticed

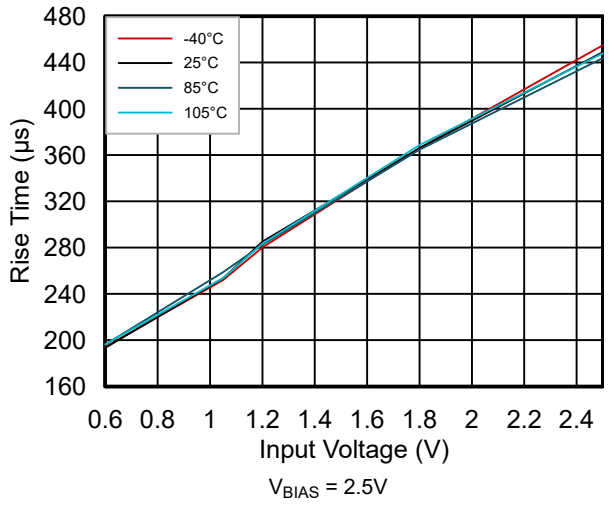


Figure 6-9. Rise Time vs Input Voltage

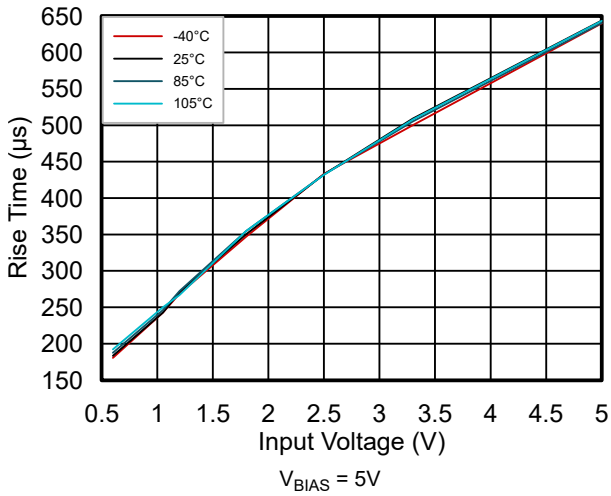


Figure 6-10. Rise Time vs Input Voltage

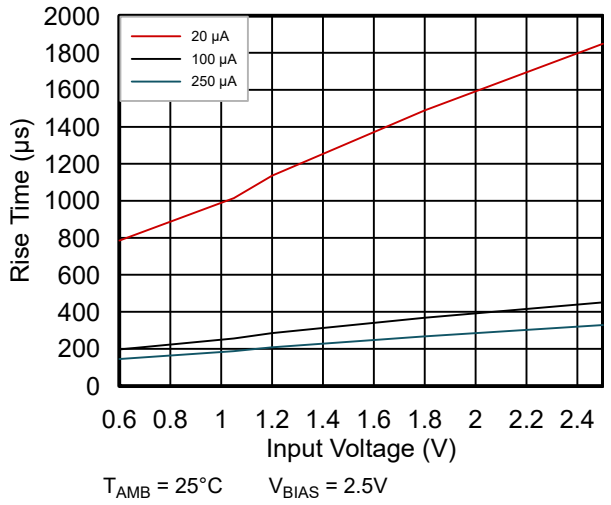


Figure 6-11. Rise Time vs Input Voltage with Different I_{ON}

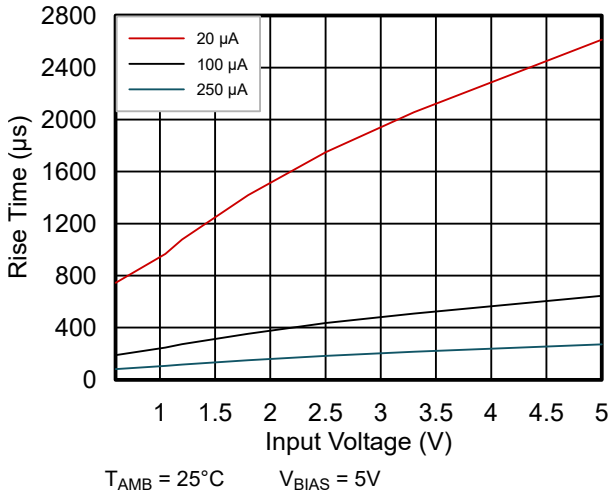


Figure 6-12. Rise Time vs Input Voltage with Different I_{ON}

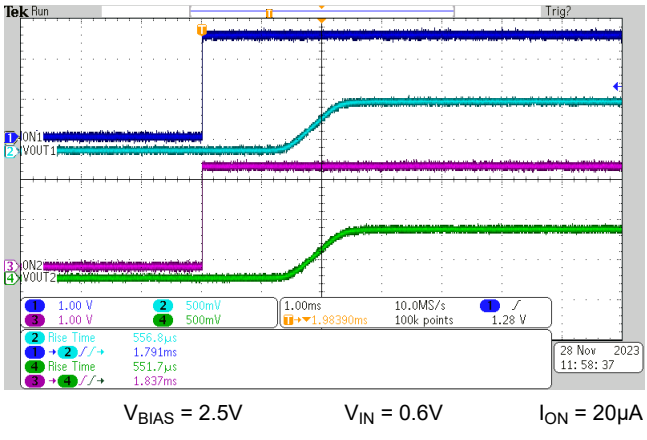


Figure 6-13. Turnon Response Time

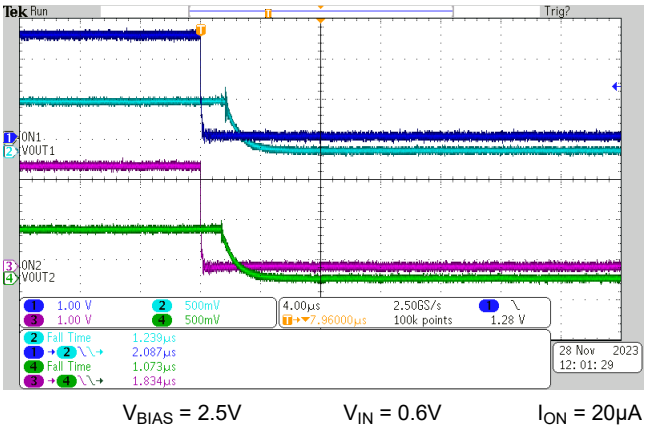
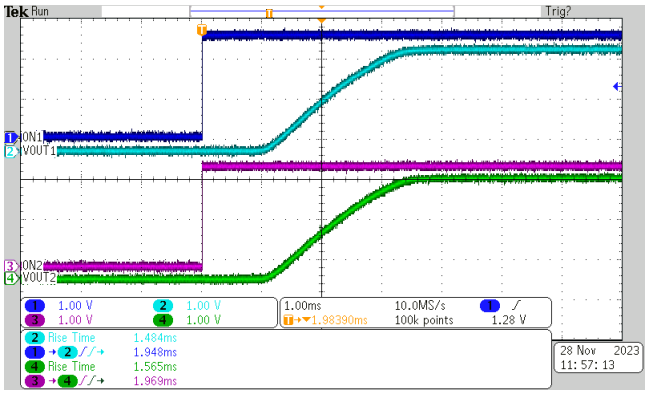


Figure 6-14. Turnoff Response Time

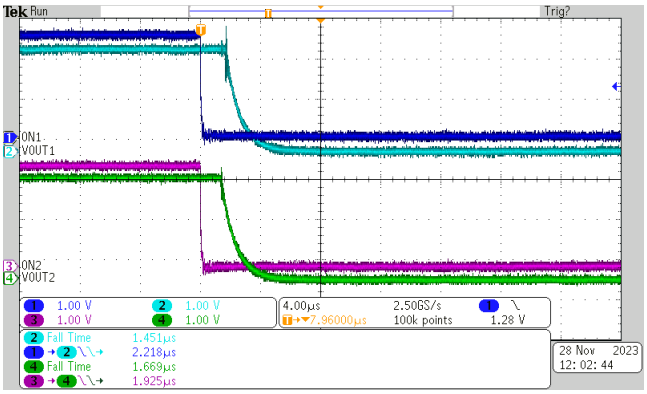
6.8 Typical Characteristics: AC (continued)

C_{IN} = 1µF, C_L = 0.1µF, R_L = 10Ω, V_{ON} = 5V, I_{ON} = 100µA unless otherwise noticed



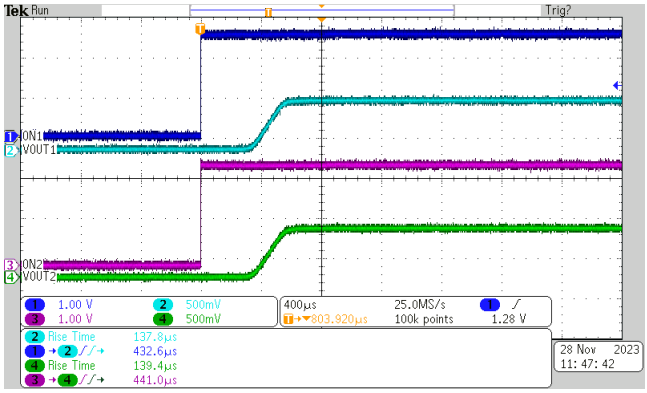
V_{BIAS} = 2.5V V_{IN} = 2.5V I_{ON} = 20µA

Figure 6-15. Turnon Response Time



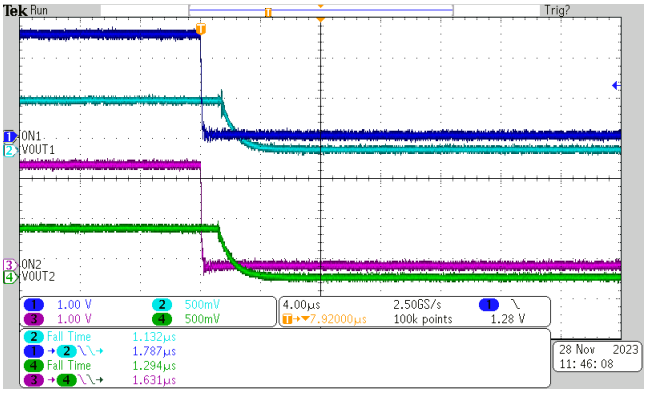
V_{BIAS} = 2.5V V_{IN} = 2.5V I_{ON} = 20µA

Figure 6-16. Turnoff Response Time



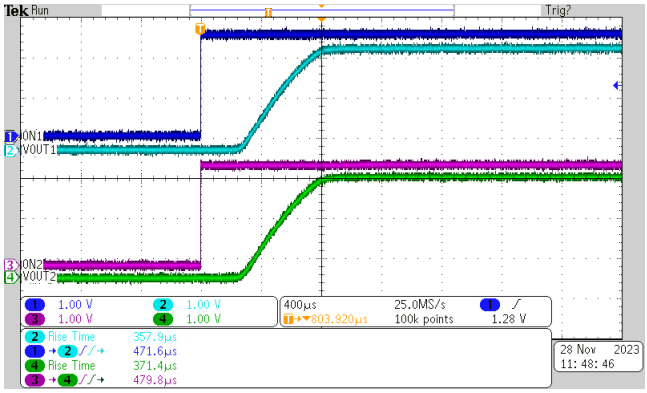
V_{BIAS} = 2.5V V_{IN} = 0.6V I_{ON} = 100µA

Figure 6-17. Turnon Response Time



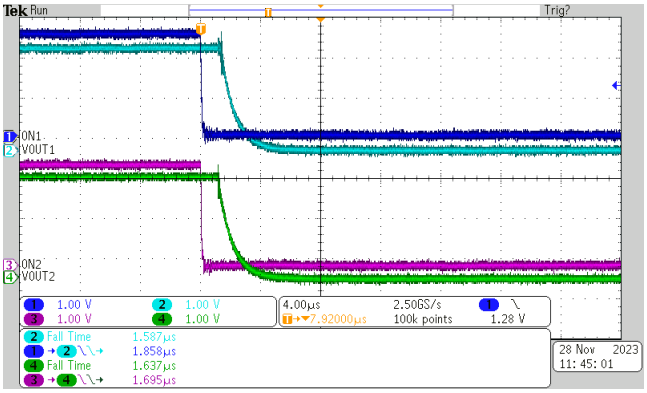
V_{BIAS} = 2.5V V_{IN} = 0.6V I_{ON} = 100µA

Figure 6-18. Turnoff Response Time



V_{BIAS} = 2.5V V_{IN} = 2.5V I_{ON} = 100µA

Figure 6-19. Turnon Response Time

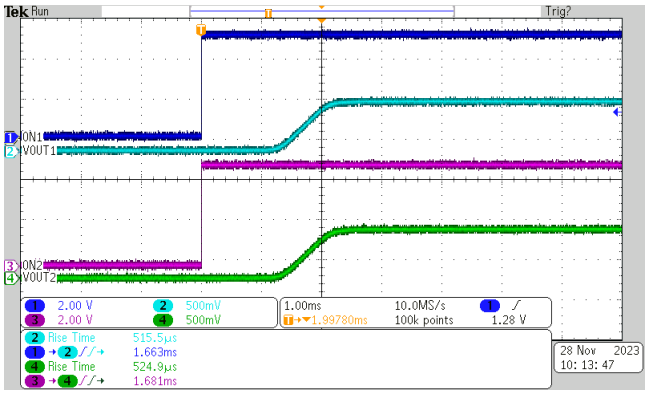


V_{BIAS} = 2.5V V_{IN} = 2.5V I_{ON} = 100µA

Figure 6-20. Turnoff Response Time

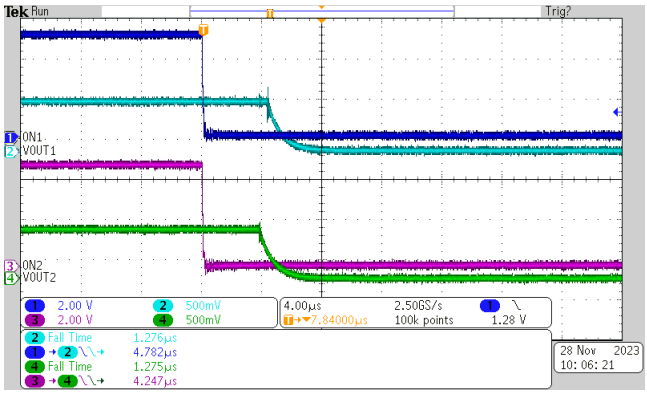
6.8 Typical Characteristics: AC (continued)

C_{IN} = 1µF, C_L = 0.1µF, R_L = 10Ω, V_{ON} = 5V, I_{ON} = 100µA unless otherwise noticed



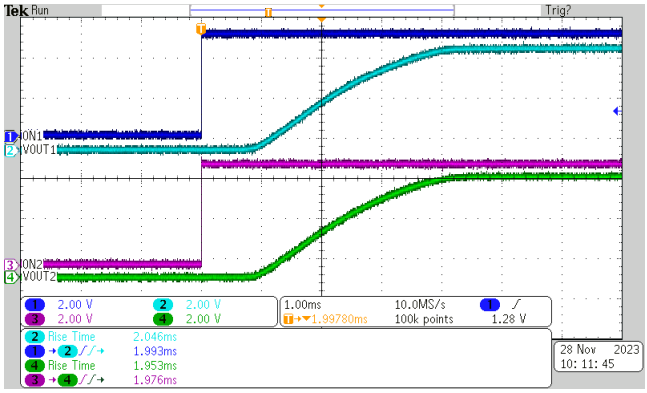
V_{BIAS} = 5V V_{IN} = 0.6V I_{ON} = 20µA

Figure 6-21. Turnon Response Time



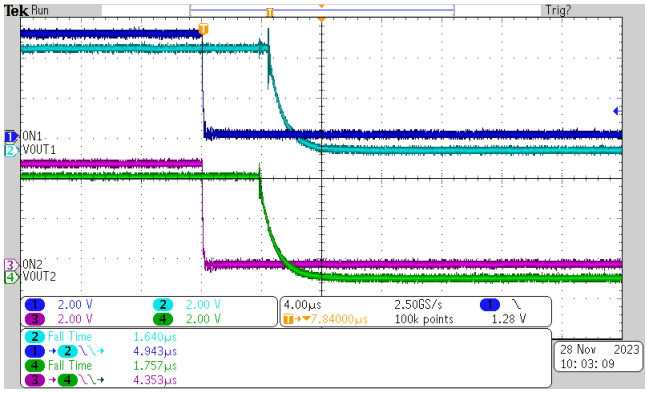
V_{BIAS} = 5V V_{IN} = 0.6V I_{ON} = 20µA

Figure 6-22. Turnoff Response Time



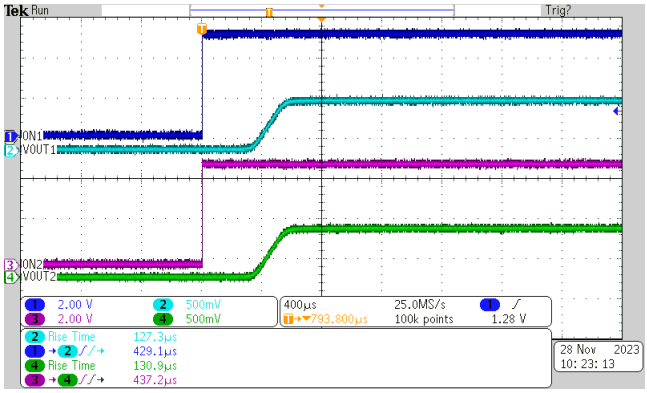
V_{BIAS} = 5V V_{IN} = 5V I_{ON} = 20µA

Figure 6-23. Turnon Response Time



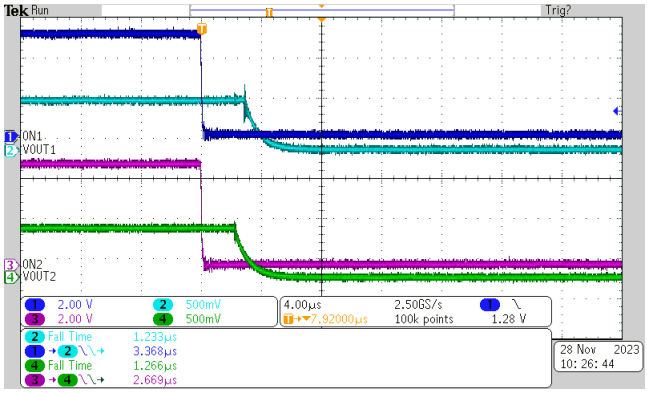
V_{BIAS} = 5V V_{IN} = 5V I_{ON} = 20µA

Figure 6-24. Turnoff Response Time



V_{BIAS} = 5V V_{IN} = 0.6V I_{ON} = 100µA

Figure 6-25. Turnon Response Time

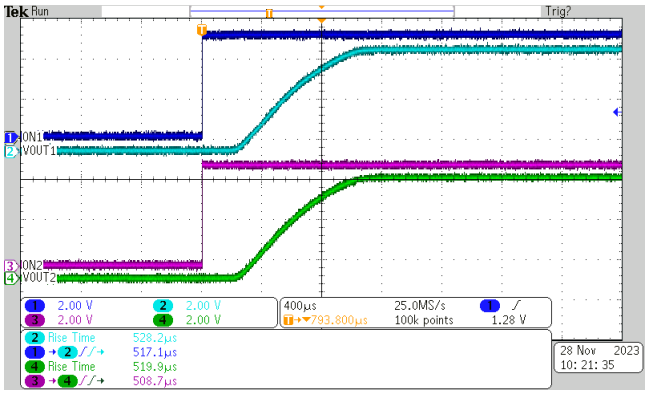


V_{BIAS} = 5V V_{IN} = 0.6V I_{ON} = 100µA

Figure 6-26. Turnoff Response Time

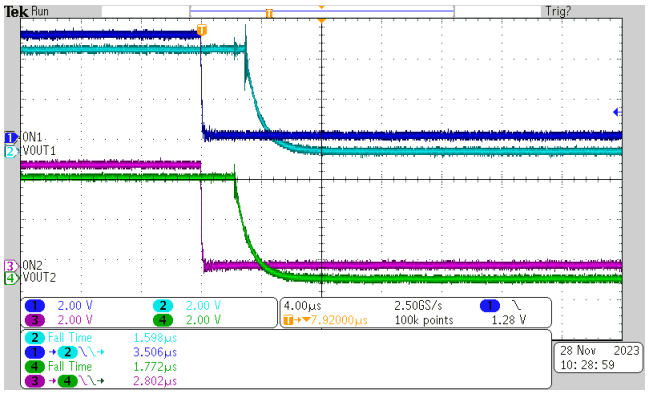
6.8 Typical Characteristics: AC (continued)

C_{IN} = 1µF, C_L = 0.1µF, R_L = 10Ω, V_{ON} = 5V, I_{ON} = 100µA unless otherwise noticed



V_{BIAS} = 5V V_{IN} = 5V I_{ON} = 100µA

Figure 6-27. Turnon Response Time



V_{BIAS} = 5V V_{IN} = 5V I_{ON} = 100µA

Figure 6-28. Turnoff Response Time

7 Parameter Measurement Information

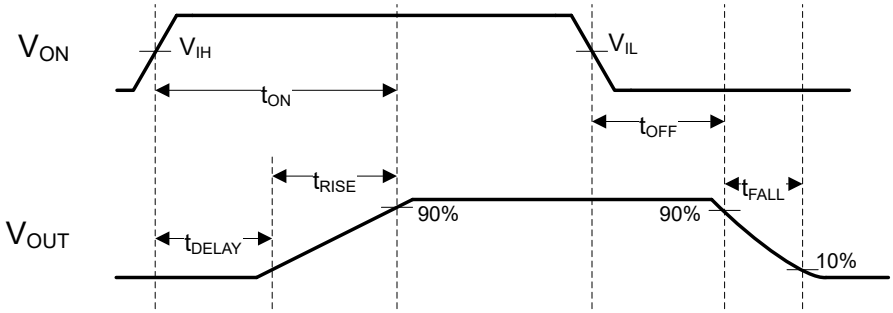


Figure 7-1. t_{ON} and t_{OFF} Waveforms

8 Detailed Description

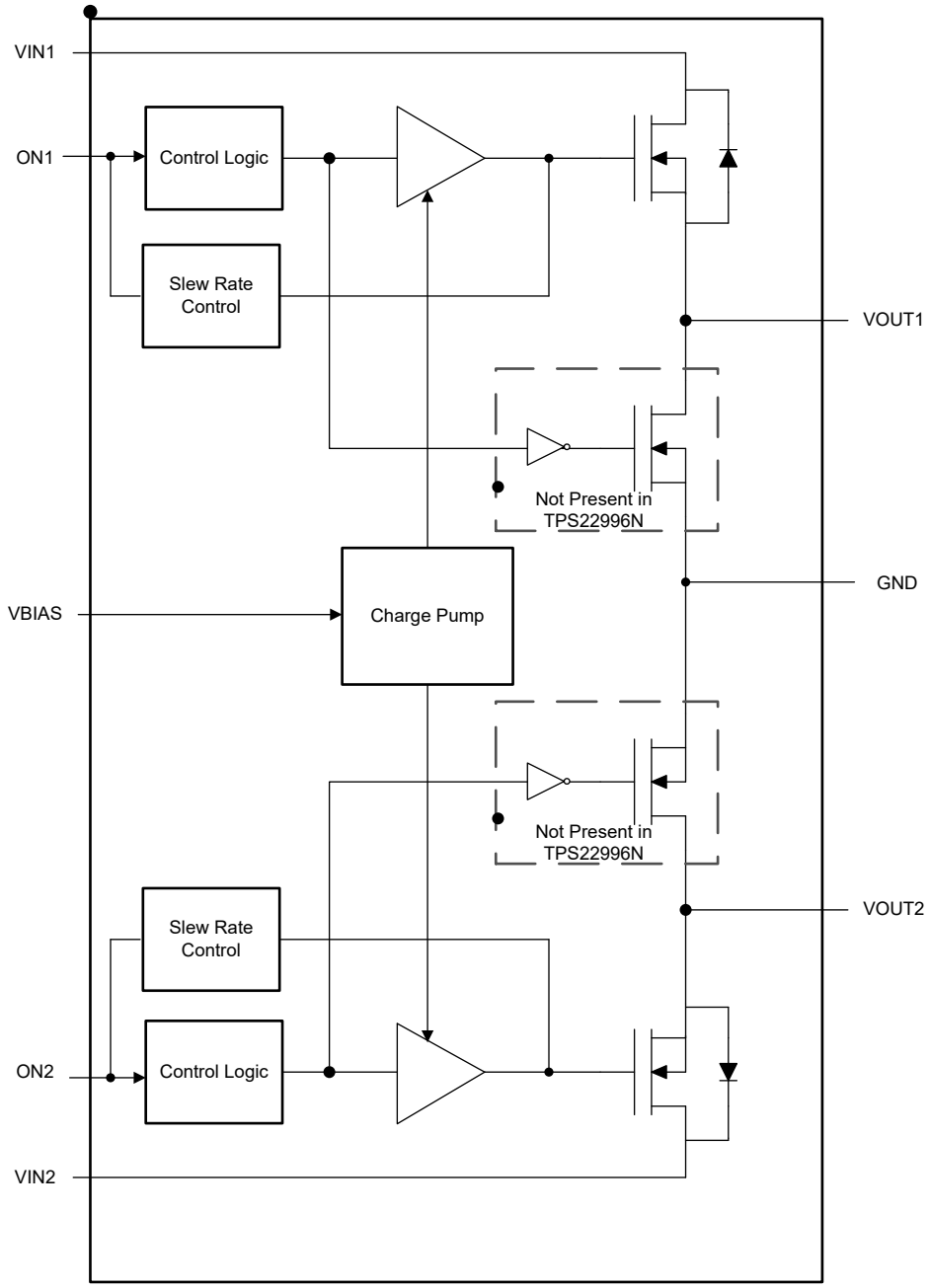
8.1 Overview

The TPS22996 is a 5.5V, dual-channel, 14mΩ (typical) R_{ON} load switch in a 8-pin DRL package. Each channel can support a maximum continuous current of 4A and is controlled by an on and off GPIO-compatible input. To reduce the voltage drop in high current rails, the device implements N-channel MOSFETs. Note that the ON pins must be connected and cannot be left floating. The device has a configurable slew rate for applications that require specific rise-time, which controls the inrush current. By controlling the inrush current, power supply sag can be reduced during turnon. Furthermore, the slew rate is proportional to the series resistor used on the ONx pin. See Section 8.3.6 to determine the correct resistor value for a desired rise time.

The internal circuitry is powered by the V_{BIAS} pin, which supports voltages from 2.5V to 5.5V. This circuitry includes the charge pump, QOD (optional), and control logic. When a voltage is applied to V_{BIAS}, and the ON_X pins transition to a low state, the QOD functionality is activated. This connects V_{OUTX} to ground through the on-chip resistor. The typical pulldown resistance (R_{PD}) is 230Ω.

During the off state, the device prevents downstream circuits from pulling high standby current from the supply. The integrated control logic, driver, power supply, and output discharge FET eliminates the need for any external components, reducing solution size and bill of materials (BOM) count.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 ON and OFF Control

The ON pins control the state of the switch and also the rise time of the output. Asserting ON high enables the switch. ON is active high with a low threshold, making it capable of interfacing with low-voltage signals. The ON pin is compatible with standard GPIO logic threshold. It can be used with any microcontroller with 1.2V or higher GPIO voltage. This pin cannot be left floating and must be tied either high or low for proper functionality.

8.3.2 Input Capacitor (Optional)

To limit the voltage drop on the input supply caused by transient inrush currents when the switch turns on into a discharged load capacitor, a capacitor needs to be placed between VIN and GND. A 1µF ceramic capacitor, C_{IN},

placed close to the pins is usually sufficient. Higher values of C_{IN} can be used to further reduce the voltage drop during high-current application. When switching heavy loads, it is recommended to have an input capacitor about 10 times higher than the output capacitor to avoid excessive voltage drop.

8.3.3 Output Capacitor (Optional)

Due to the integrated body diode in the NMOS switch, a C_{IN} greater than C_L is highly recommended. A C_L greater than C_{IN} can cause V_{OUT} to exceed V_{IN} when the system supply is removed. This could result in current flow through the body diode from VOUT to VIN. A C_{IN} to C_L ratio of 10 to 1 is recommended for minimizing V_{IN} dip caused by inrush currents during startup, however a 10 to 1 ratio for capacitance is not required for proper functionality of the device. A ratio smaller than 10 to 1 (such as 1 to 1) could cause slightly more V_{IN} dip upon turnon due to inrush currents. This can be mitigated by increasing the capacitance on the RT resistor for a longer rise time (see Section 8.3.6).

8.3.4 Quick Output Discharge (QOD)

The TPS22996 includes a QOD feature. When the switch V_{ONX} is disabled, an internal discharge resistance is connected between V_{OUTX} and GND to remove the remaining charge from the output. This resistance prevents the output from floating while the switch is disabled. For best results, it is recommended that the device gets disabled before V_{BIAS} falls below the minimum recommended voltage.

8.3.5 Thermal Shutdown

Thermal Shutdown protects the part from internally or externally generated excessive temperatures. When the device temperature exceeds T_{SD}, the switch is turned off. The switch automatically turns on again if the temperature of the die drops below hyteresis.

8.3.6 Adjustable Rise Time

TPS22996 integrates a unique architecture for adjusting the rise time. The device senses the current flowing into the ON1 and ON2 (I_{ON}) pins and utilizes the information to set the rise time. This allows the user to adjust the rise time by connecting a series resistance that is determined by the ON Pin voltage. Refer to Table 8-1 and Table 8-2 for reference on setting the resistor.

Table 8-1. Typical Rise Time (V_{BIAS} = 5.0V, R_L = 10Ω, C_L = 0.1µF)

I_{ON}	V_{IN} = 0.6V	V_{IN} = 1.8V	V_{IN} = 2.5V	V_{IN} = 3.3V	VIN = 5.0V
20µA	810µs	1434µs	1760µs	1986µs	2580µs
100µA	215µs	364µs	445µs	519µs	688µs
250µA	90µs	151µs	185µs	220µs	291µs

Table 8-2. Typical Rise Time (V_{BIAS} = 3.3V, R_L = 10Ω, C_L = 0.1µF)

I_{ON}	V_{IN} = 0.6V	V_{IN} = 1.8V	V_{IN} = 2.5V	V_{IN} = 3.3V
20µA	781µs	1489µs	1821µs	2154µs
100µA	200µs	374µs	451µs	536µs
250µA	93µs	175µs	207µs	244µs

The following equation can be used to estimate the series resistance required to meet the desired rise time.

$$R_T = 1000 \times (V_{ON} - 1.2V) / I_{ON} - R_i \quad (1)$$

where:

- R_T = Series resistance in kΩ.
- R_i = Internal On Pin resistance in kΩ.
- V_{ON} = ON pin voltage in V.
- I_{ON} = Current flowing into the ON pin in µA.

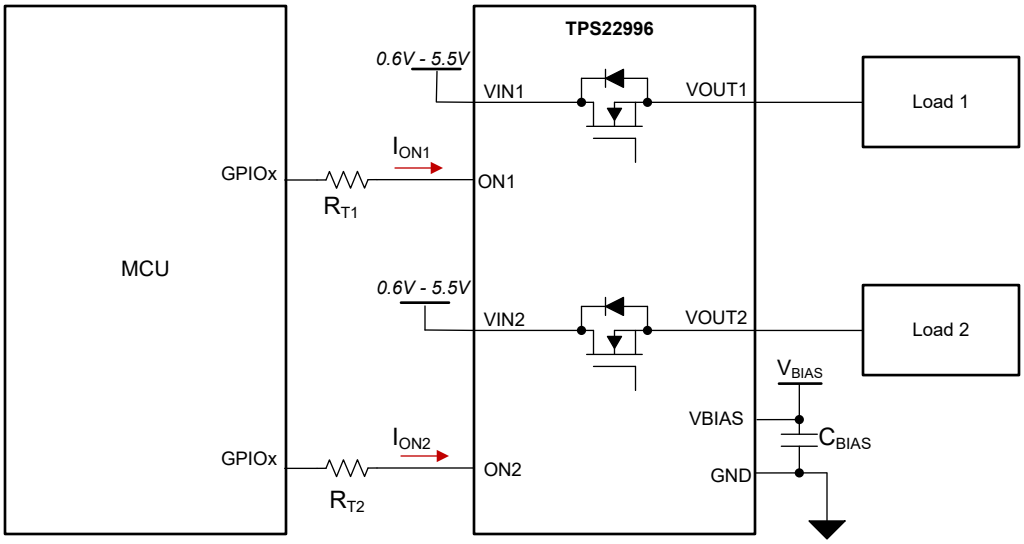


Figure 8-1. TPS22996 Adjustable Rise Time Configuration

8.4 Device Functional Modes

Table 8-3 lists the TPS22996 functions.

Table 8-3. TPS22996 Functions Table

ON	VIN to VOUT	VOUT
L	Off	GND
H	On	VIN

Table 8-4 lists the TPS22996N functions.

Table 8-4. TPS22996N Functions Table

ON	VIN to VOUT	VOUT
L	Off	Floating
H	On	VIN

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

This section highlights some of the design considerations for implementing the device in various applications.

9.2 Typical Application

This application demonstrates how the TPS22996 can be used to limit the inrush current when powering on downstream modules.

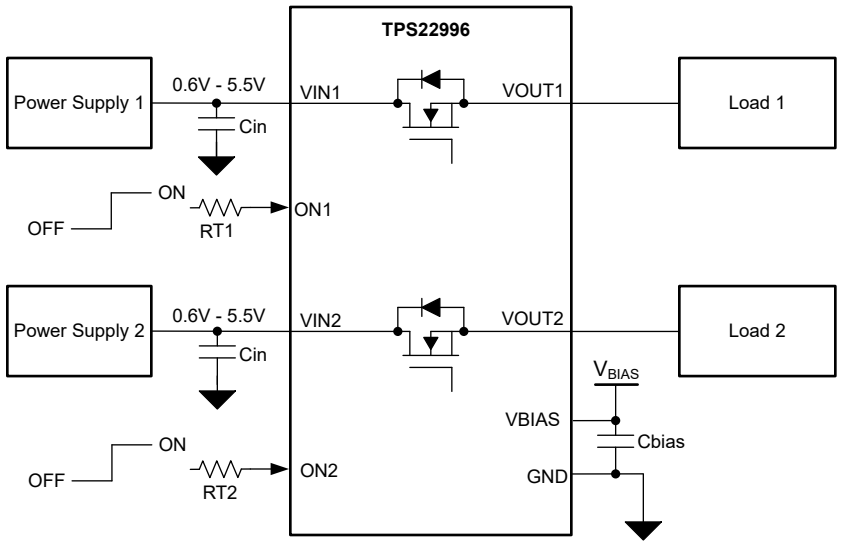


Figure 9-1. Typical Application Circuit

Table 9-1. Component Descriptions

DESIGN PARAMETER	TYPICAL VALUES	DESCRIPTION
C_{IN}	1µF	Filtering voltage transients
C_{OUT}	100nF	Filtering voltage transients
C_{BIAS}	0.1µF	Filtering voltage transients and noises
RT1, RT2	10kΩ	Series resistor for rise time control

9.2.1 Design Requirements

For this example, the values below are used as the design parameters.

Table 9-2. Design Parameters

PARAMETER	VALUE
V_{BIAS}	5V
V_{IN}	5V
Rise Time	1000µs

9.2.2 Detailed Design Procedure

The design in this example is trying to achieve 1000µs rise time for power sequencing, with both V_{BIAS} and V_{IN} to be 5V. From Table 8-1, the I_{ON} needs to be between 20µA and 100µA. To find the I_{ON} needed to achieve 1000µs rise time, linear interpolation can be used to estimate as below:

$$T_R = (T_{R2} - T_{R1}) / (I_{ON2} - I_{ON1}) * (I_{ON} - I_{ON1}) + T_{R1} \quad (2)$$

where:

- T_R is the desired T_R, which is 1000µs
- I_{ON} is the desired I_{ON}
- T_{R1} is the first T_R used for linear interpolation, which is 2580µs
- T_{R2} is the second T_R used for linear interpolation, which is 688µs
- I_{ON1} is the first I_{ON} used for linear interpolation, which is 20µA
- I_{ON2} is the second I_{ON} used for linear interpolation, which is 100µA

I_{ON} is calculated to be 86.8µA. To find the R_T value, plug in the parameters in Equation 1.

$R_T = 1000 \times (5V - 1.2V) / 86.8µA - 11.5kΩ = 32.2kΩ$

By using the standard resistor value closest to 32.2kΩ, the typical rise time can be calculated for the actual resistor value used on board.

9.3 Power Supply Recommendations

The device is designed to operate from a V_{BIAS} range of 2.5V to 5.7V and a V_{IN} range of 0.6V to V_{BIAS}.

9.4 Layout

9.4.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, the input and output capacitors must be placed close to the device to minimize the effects that parasitic trace inductances may have on normal operation. Using wide traces for V_{IN}, V_{OUT}, and GND helps minimize the parasitic electrical effects along with minimizing the case to ambient thermal impedance.

9.4.2 Layout Example

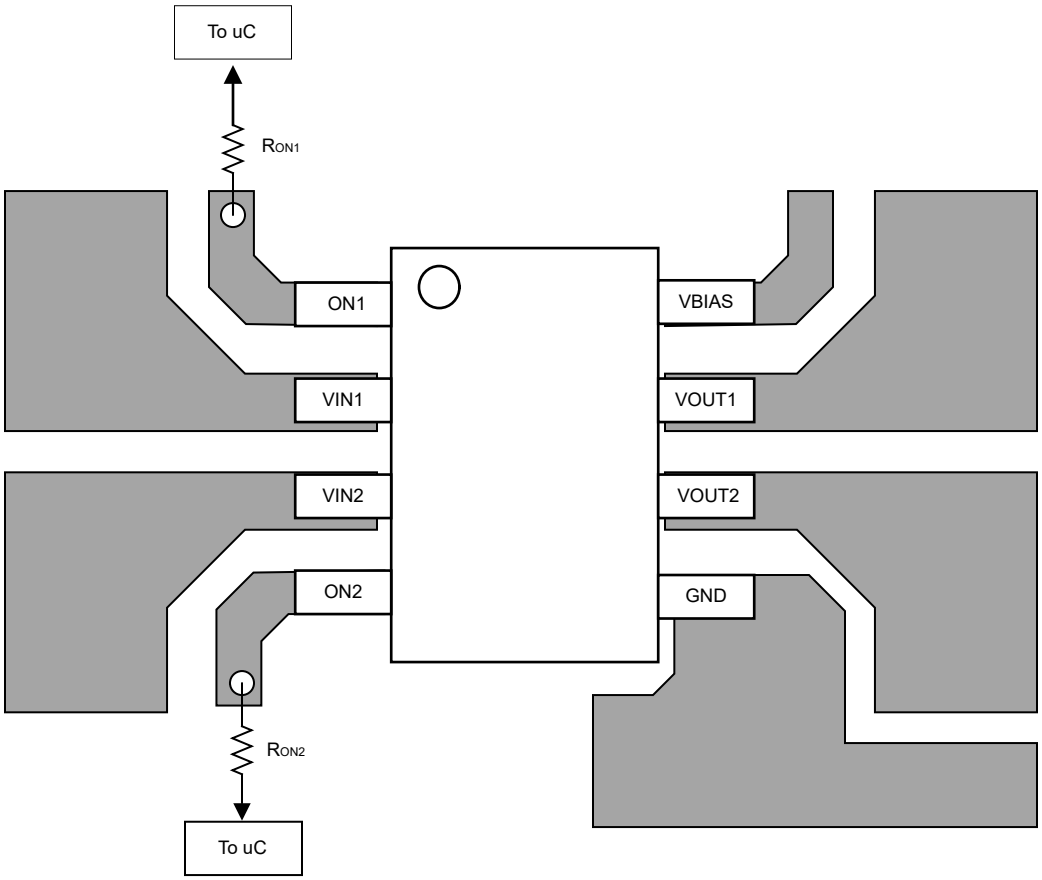


Figure 9-2. TPS22996 Layout Example

9.4.3 Power Dissipation

The maximum IC junction temperature must be restricted to 125°C under normal operating conditions. To calculate the maximum allowable power dissipation, $P_{D(max)}$ for a given output current and ambient temperature, use Equation 3.

$$P_{D(max)} = \frac{T_{J(max)} - T_A}{\theta_{JA}} \quad (3)$$

where

- $P_{D(max)}$ is the maximum allowable power dissipation.
- $T_{J(max)}$ is the maximum allowable junction temperature (125°C for the TPS22996).

- T_A is the ambient temperature of the device.
- θ_{JA} is the junction to air thermal impedance. See the *Thermal Information* section. This parameter is highly dependent upon board layout.

10 Device and Documentation Support

10.1 Third-Party Products Disclaimer

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10.2 Receiving Notification of Documentation Updates

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10.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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10.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

10.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

11 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision * (December 2023) to Revision A (August 2025)	Page
• Changed TPS22996N from preview status to production	3

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS22996DRLR	Active	Production	SOT-5X3 (DRL) | 8	4000 | LARGE T&R	Yes	Call TI | Sn	Level-1-260C-UNLIM	-40 to 105	22996
TPS22996DRLR.A	Active	Production	SOT-5X3 (DRL) | 8	4000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 105	22996
TPS22996DRLR.B	Active	Production	SOT-5X3 (DRL) | 8	4000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 105	22996

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

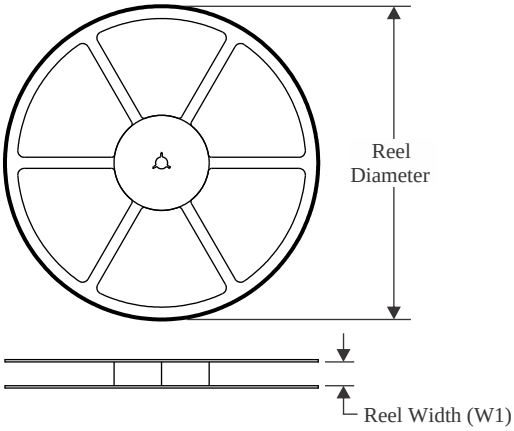
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

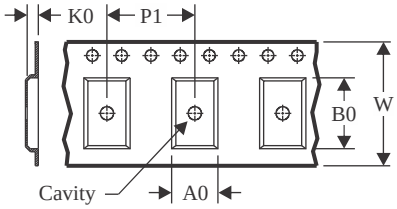
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

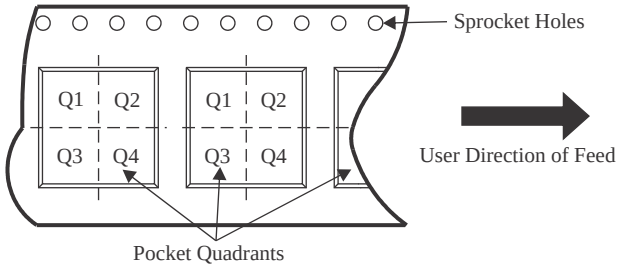


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

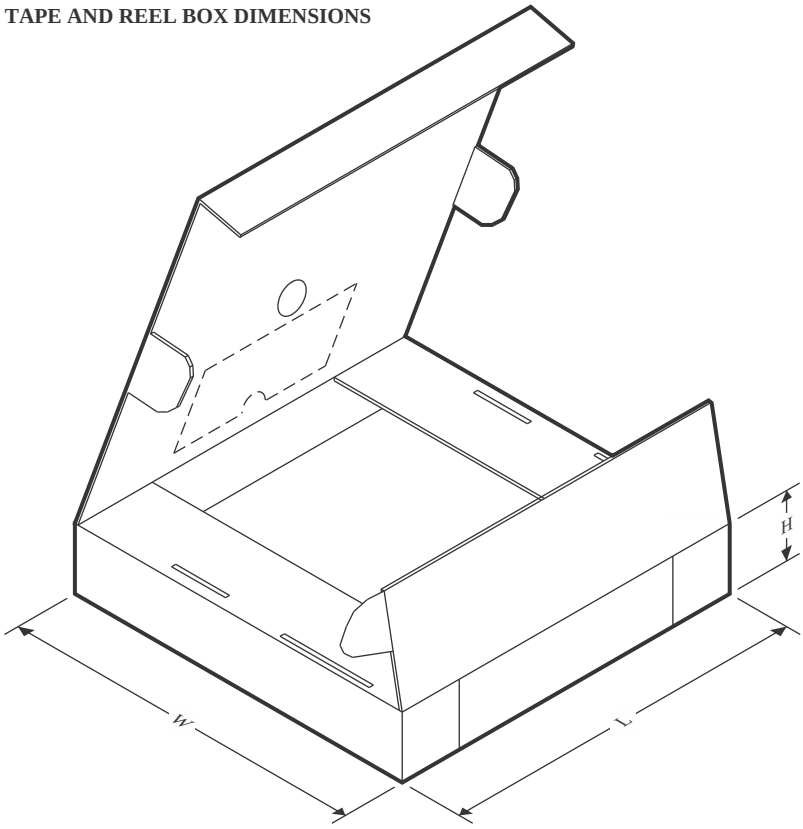
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPS22996DRLR	SOT-5X3	DRL	8	4000	180.0	8.4	2.75	1.9	0.8	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

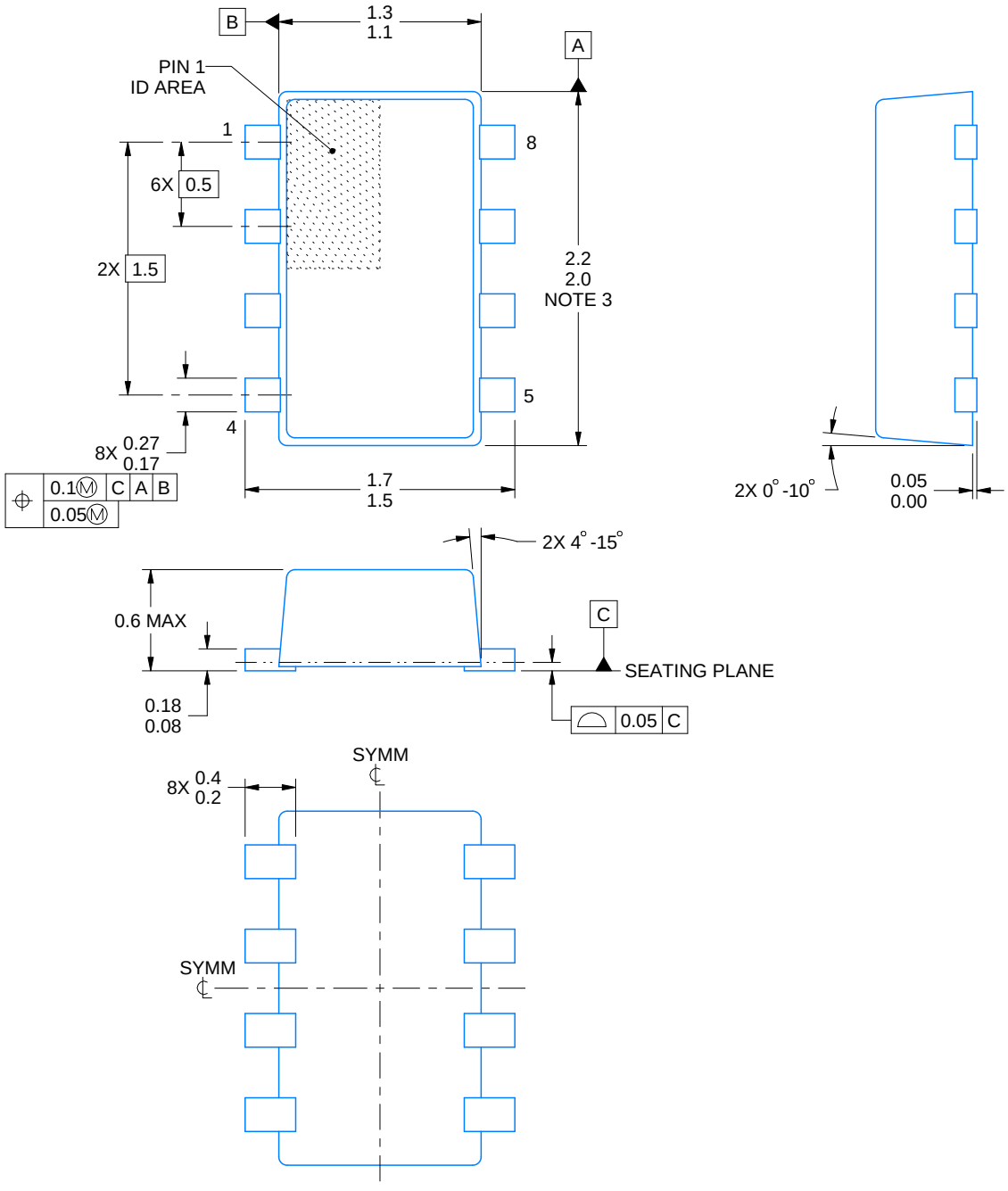
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPS22996DRLR	SOT-5X3	DRL	8	4000	210.0	185.0	35.0

PACKAGE OUTLINE

DRL0008A

SOT-5X3 - 0.6 mm max height

PLASTIC SMALL OUTLINE



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NOTES:

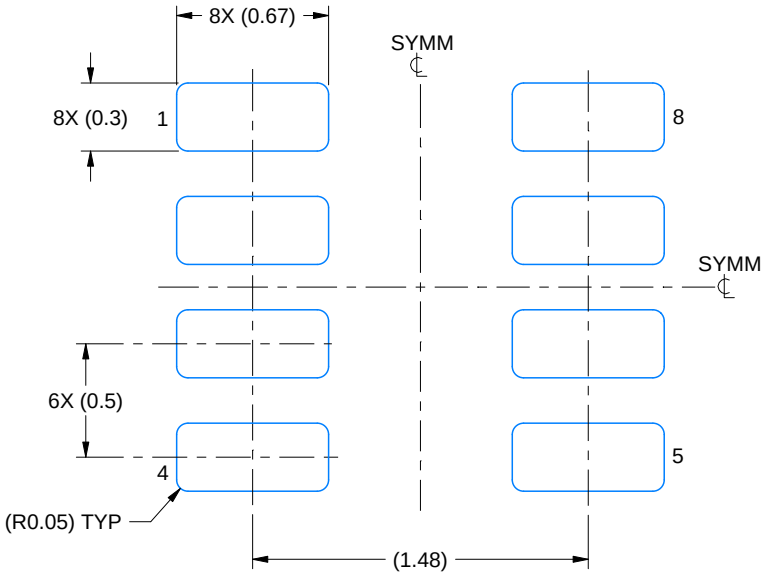
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. Reference JEDEC Registration MO-293, Variation UDAD

EXAMPLE BOARD LAYOUT

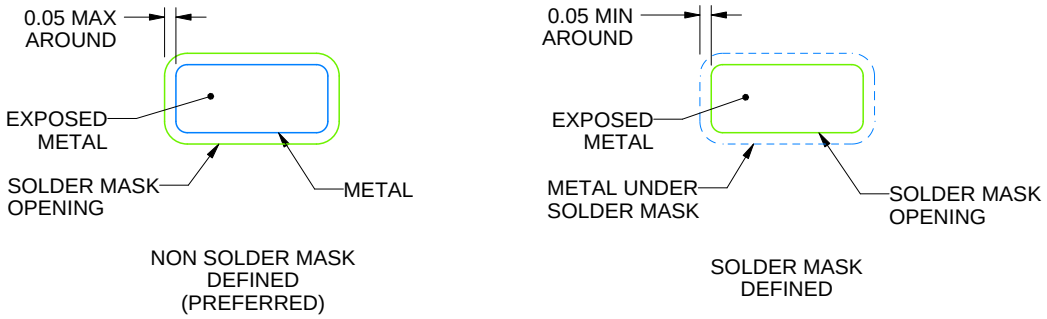
DRL0008A

SOT-5X3 - 0.6 mm max height

PLASTIC SMALL OUTLINE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:30X



SOLDERMASK DETAILS

4224486/G 11/2024

NOTES: (continued)

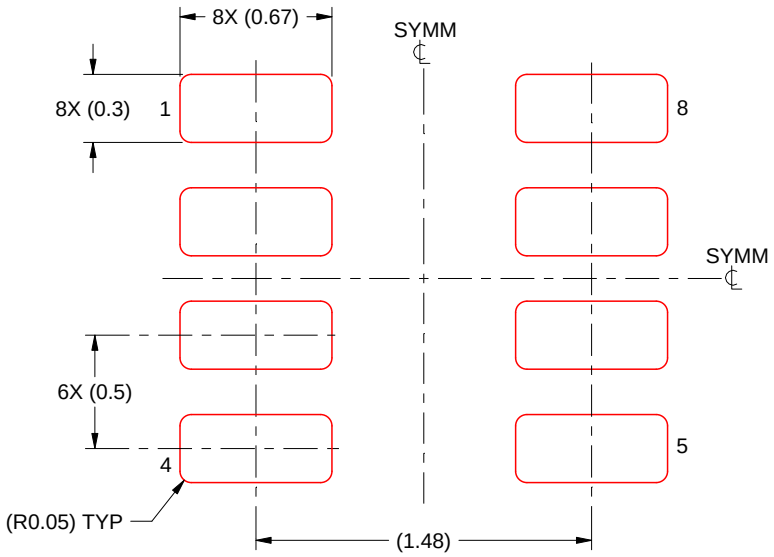
5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
7. Land pattern design aligns to IPC-610, Bottom Termination Component (BTC) solder joint inspection criteria.

EXAMPLE STENCIL DESIGN

DRL0008A

SOT-5X3 - 0.6 mm max height

PLASTIC SMALL OUTLINE



SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

4224486/G 11/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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